

**IN THE CLAIMS:**

Please amend claim 14 as follows.

14. (Amended) A method of manufacturing a semiconductor device, the method comprising:

depositing a layer of dielectric material, having an as-deposited dielectric constant no greater than about 3, over a conductive region or conductive feature;

forming a photoresist mask on the layer of dielectric material;

forming a through-hole in the dielectric layer exposing the upper surface of the conductive region or conductive feature; and

removing the photoresist mask and cleaning the through-hole with a plasma containing carbon tetrafluoride (CF<sub>4</sub>) and water vapor (H<sub>2</sub>O) such that the dielectric constant of the dielectric layer does not increase more than about 15%.

**REMARKS**

Claims 1 through 3, 5 through and 16 through 20 are pending in this application. The specification has been amended consistent with the Examiner's suggestion. In addition, claim 4 has been amended to provide antecedent bases for the photoresist mask as observed by the Examiner. Applicants submit that the present Amendment does not generate any new matter issue.

A clean copy of the paragraphs of the specification affected by the present Amendment and of amended claim 14 appears in the Appendix hereto.

**Claim 14 was rejected the second paragraph of 35 U.S.C. §112.**